

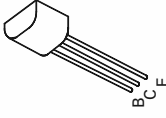
# NPN SILICON PLANAR MEDIUM POWER DARLINGTON TRANSISTOR

## FXT605

ISSUE 1 – SEPT 93

### FEATURES

- \* 120 Volt  $V_{CE0}$
  - \* Gain of 2K at  $I_C=1$  Amp
  - \*  $P_{tot}=1$  Watt
- ### APPLICATIONS
- \* Lamp, solenoid and relay drivers
  - \* Replacement of TO126 and TO220 packages
- REFER TO ZTX605 FOR GRAPHS



E-Line  
TO92 Compatible

### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	140	V
Collector-Emitter Voltage	$V_{CEO}$	120	V
Emitter-Base Voltage	$V_{EBO}$	10	V
Peak Pulse Current	$I_{CM}$	4	A
Continuous Collector Current	$I_C$	1	A
Power Dissipation at $T_{amb} = 25^\circ\text{C}$	$P_{tot}$	1	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	140			V	$I_C=100\mu\text{A}, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	120			V	$I_C=10\text{mA}, I_B=0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	10			V	$I_E=100\mu\text{A}, I_C=0$
Collector Cut-Off Current	$I_{CBO}$		0.01 10		$\mu\text{A}$ $\mu\text{A}$	$V_{CB}=120\text{V}, I_E=0$ $V_{CB}=120\text{V}, T_{amb}=100^\circ\text{C}$
Emitter Cut-Off Current	$I_{EBO}$		0.1		$\mu\text{A}$	$V_{EB}=8\text{V}, I_C=0$
Collector-Emitter Cut-Off Current	$I_{CES}$		10		$\mu\text{A}$	$V_{CES}=120\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		1.0 1.5		V V	$I_C=0.25\text{A}, I_B=0.25\text{mA}^*$ $I_C=1\text{A}, I_B=1\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.8		V	$I_C=1\text{A}, I_B=1\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		1.7		V	$I_C=1\text{A}, V_{CE}=5\text{V}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	2000 5000 2000 500		100K		$I_C=50\text{mA}, V_{CE}=5\text{V}^*$ $I_C=500\text{mA}, V_{CE}=5\text{V}^*$ $I_C=1\text{A}, V_{CE}=5\text{V}^*$ $I_C=2\text{A}, V_{CE}=5\text{V}^*$
Transition Frequency	$f_T$	150			MHz	$I_C=100\text{mA}, V_{CE}=10\text{V}$ $f=20\text{MHz}$

\* Measured under pulse conditions. Pulse width=300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$

查询FXT605供应商

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